

# UNISONIC TECHNOLOGIES CO., LTD

2SK3557 **Preliminary JFET** 

# FIELD EFFECT TRANSISTOR SILICON N-CHANNEL JUNCTION TYPE

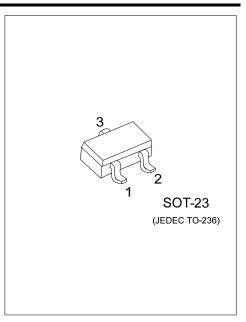
#### DESCRIPTION

The UTC 2SK3557 is an N-channel junction silicon FET, it uses UTC's advanced technology to provide the customers with low IGSS and low CRSS.

The UTC 2SK3557 is suitable for audio frequency low noise amplifier, impedance conversion, infrared sensor applications.

#### **FEATURES**

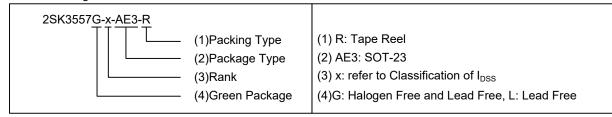
- \* Small Ciss
- \* Ultralow Noise Figure
- \* High breakdown voltage: V<sub>GDS</sub>=-15V
- \* High input impedance: IGSS=-1nA (max) at VGS=-10V



#### ORDERING INFORMATION

| Ordering         | Number           | Daalaaaa | Pin Assignment |   |   | Da alsinan |  |
|------------------|------------------|----------|----------------|---|---|------------|--|
| Lead Free        | Halogen Free     | Package  | 1              | 2 | 3 | Packing    |  |
| 2SK3557L-x-AE3-R | 2SK3557G-x-AE3-R | SOT-23   | S              | D | G | Tape Reel  |  |

Note: Pin Assignment: S: Source D: Drain G: Gate



#### **MARKING**



### ■ ABSOLUTE MAXIMUM RATINGS (T<sub>C</sub>=25°C, unless otherwise specified)

| PARAMETER                   | SYMBOL           | RATINGS    | UNIT |
|-----------------------------|------------------|------------|------|
| Drain-Source Voltage        | $V_{DSX}$        | 15         | V    |
| Gate-Drain Voltage          | $V_{GDS}$        | -15        | ٧    |
| Gate Current                | I <sub>G</sub>   | 10         | mA   |
| Drain Current               | $I_D$            | 50         | mA   |
| Power Dissipation           | $P_D$            | 200        | mW   |
| Junction Temperature        | $T_J$            | +150       | Ŝ    |
| Operating Temperature Range | T <sub>OPR</sub> | -40 ~ +125 | Ŝ    |
| Storage Temperature Range   | T <sub>STG</sub> | -55 ~ +125 | Ŝ    |

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

#### ■ ELECTRICAL CHARACTERISTICS (Tc=25°C, unless otherwise specified)

| i e                          | 1                    | <del> </del>   | 1    |      | 1    | 1 1  |
|------------------------------|----------------------|--|------|------|------|------|
| PARAMETER                    | SYMBOL               | TEST CONDITIONS  | MIN  | TYP  | MAX  | UNIT |
| OFF CHARACTERISTICS          |                      |  |      |      |      |      |
| Gate Cut-off Current         | Igss                 | V <sub>GS</sub> =-10V, V <sub>DS</sub> =0V                       |      |      | -1.0 | nA   |
| Gate-Drain Breakdown Voltage | V <sub>(BR)GDS</sub> | I <sub>G</sub> =-10μA, V <sub>DS</sub> =0V                       | -15  |      |      | V    |
| Drain-Source Leakage Current | I <sub>DSS</sub>     | V <sub>DS</sub> =5V, V <sub>GS</sub> =0V                         | 10   |      | 32   | mA   |
| Forward Transfer Admittance  | yfs                  | V <sub>DS</sub> =5V, V <sub>GS</sub> =0V, f=1kHz                 | 24   | 35   |      | mS   |
| ON CHARACTERISTICS           |                      |  |      |      |      |      |
| Cutoff Voltage               | V <sub>GS(OFF)</sub> | V <sub>DS</sub> =5V, I <sub>D</sub> =100μA                       | -0.3 | -0.7 | -1.5 | V    |
| DYNAMIC PARAMETERS           |                      |  |      |      |      |      |
| Input Capacitance            | Ciss                 | V <sub>DS</sub> =5V, V <sub>GS</sub> =0V, f=1MHz                 |      | 12   |      | pF   |
| Reverse Transfer Capacitance | Crss                 | V <sub>DG</sub> =5V, I <sub>D</sub> =0A, f=1MHz                  |      | 6    |      | Pf   |
| Noise Figure                 | NF                   | $V_{DG}$ =5 $V$ , $R_G$ =1 $k\Omega$ , $I_D$ =1 $mA$ , f=1 $MHz$ |      | 1    |      | dB   |

## ■ CLASSIFICATION OF I<sub>DSS</sub>

| RANK  | 6       | 7       |  |  |
|-------|---------|---------|--|--|
| RANGE | 10 ~ 20 | 16 ~ 32 |  |  |

UTC assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all UTC products described or contained herein. UTC products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. UTC reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.